2023년 2월 15일(수), 10:45-12:30
Room E (루비 II, 5층)

E. Compound Semiconductors 분과
[WE2-E] Compound Semiconductor II

좌장: 차호영 교수(홍익대학교)

WE2-E-1 **10:45-11:15** **[초청]**	**Near-Junction Thermal Management for High-Power Electronics** Jungwan Cho *School of Mechanical Engineering, Sungkyunkwan University*
WE2-E-2 **11:15-11:30**	**Impact of $Hf_xAl_{1-x}O$ Gate Dielectric in the Performance Enhancement of AlGaN/GaN High Electron Mobility Transistors** Ju-Won Shin[1], Walid Amir[1], Surajit Chakraborty[1], Atish Bhattacharjee[1], Hyo-Joung Kim[1], Jae-Moo Kim[2], and Tae-Woo Kim[1] *[1]School of Electrical, Electronic, and Computer Engineering, University of Ulsan, [2]KANC*
WE2-E-3 **11:30-11:45**	**Cryogenic Switches based on InGaAs HEMT for Quantum Signal Routing** Jaeyong Jeong[1], Seong Kwang Kim[1], Jongmin Kim[2], Jisung Lee[3], Joon Pyo Kim[1], Bong Ho Kim[1], Yoon-Je Suh[1], Dae-Myeong Geum[1], Seung-Young Park[3], and SangHyeon Kim[1] *[1]School of Electrical Engineering, KAIST, [2]KANC, [3]KBSI*
WE2-E-4 **11:45-12:00**	**$In_{0.53}Ga_{0.47}As$ MOS Interface Optimization Using Post Deposition Annealing and Post Metal Annealing for Photo-FET on Si Wafer** Sung-Han Jeon[1,2], Dae-Hwan Ahn[1], Jindong Song[1], Woo-Young Choi[2], and Jae-Hoon Han[1] *[1]Center for Opto-Electronic Materials and Devices, KIST, [2]Department of Electrical and Electronic Engineering, Yonsei University*
WE2-E-5 **12:00-12:15**	**Positive–Bias–Stress Instability Assessment of AlGaN/GaN HEMTs during On-State Condition** Walid Amir[1], Ju-Won Shin[1], Ki-Yong Shin[1], Surajit Chakraborty[1], Takuya Hoshi[2], Takuya Tsutsumi[2], Hiroki Sugiyama[2], Hideaki Matsuzaki[2], and Tae-Woo Kim[1] *[1]Department of Electrical, Electronic, and Computer Engineering, University of Ulsan, [2]NTT Device Technology Laboratories, NTT Corporation*
WE2-E-6 **12:15-12:30**	**Study of Delta-doping Dopants on GaAs Tunnel Junctions and Their Thermal Degradation toward High Efficiency III-V/Si Tandem Cell** May Angelu Madarang[1,2], Rafael Jumar Chu[1,2], Yeonhwa Kim[1,3], Eunkyo Ju[1], Quang Nhat Dang Lung[1,2], Tae Soo Kim[1,4], Won Jun Choi[1], and Daehwan Jung[1,2] *[1]Center for Opto-Electronic Materials and Devices, KIST, [2]Division of Nano and Information Technology, University of Science and Technology (UST), [3]Department of Materials Science and Engineering, Korea University, [4]School of Electrical and Electronic Engineering, Yonsei University*